



Robust Systems for Scaled CMOS and Beyond

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Acknowledgment: Students & Collaborators

Robust System Design

Perform correctly despite complexity & disturbances

- **Complexity:** detect & fix design bugs
- **CMOS reliability limits:** tolerate errors
- **Beyond silicon-CMOS:** imperfection-immune logic

What's New ?

- Existing approaches: inadequate, expensive

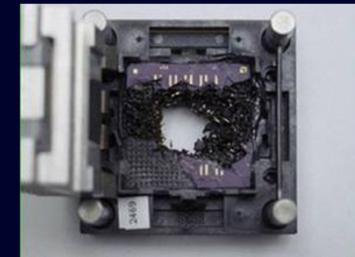
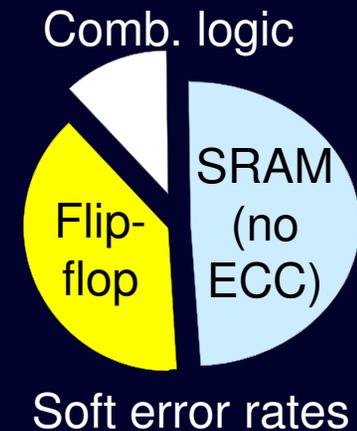
	Traditional Thinking	New approach
Design bugs	Pre-silicon	Post-silicon
Reliability failures	Avoid	Tolerate at <u>low cost</u>
Beyond silicon-CMOS	Material processing	Imperfection-immune design

Outline

- Introduction
- CMOS reliability limits: tolerate errors
- Beyond silicon-CMOS: imperfection-immune logic
- Conclusion

Technology Reliability Challenges

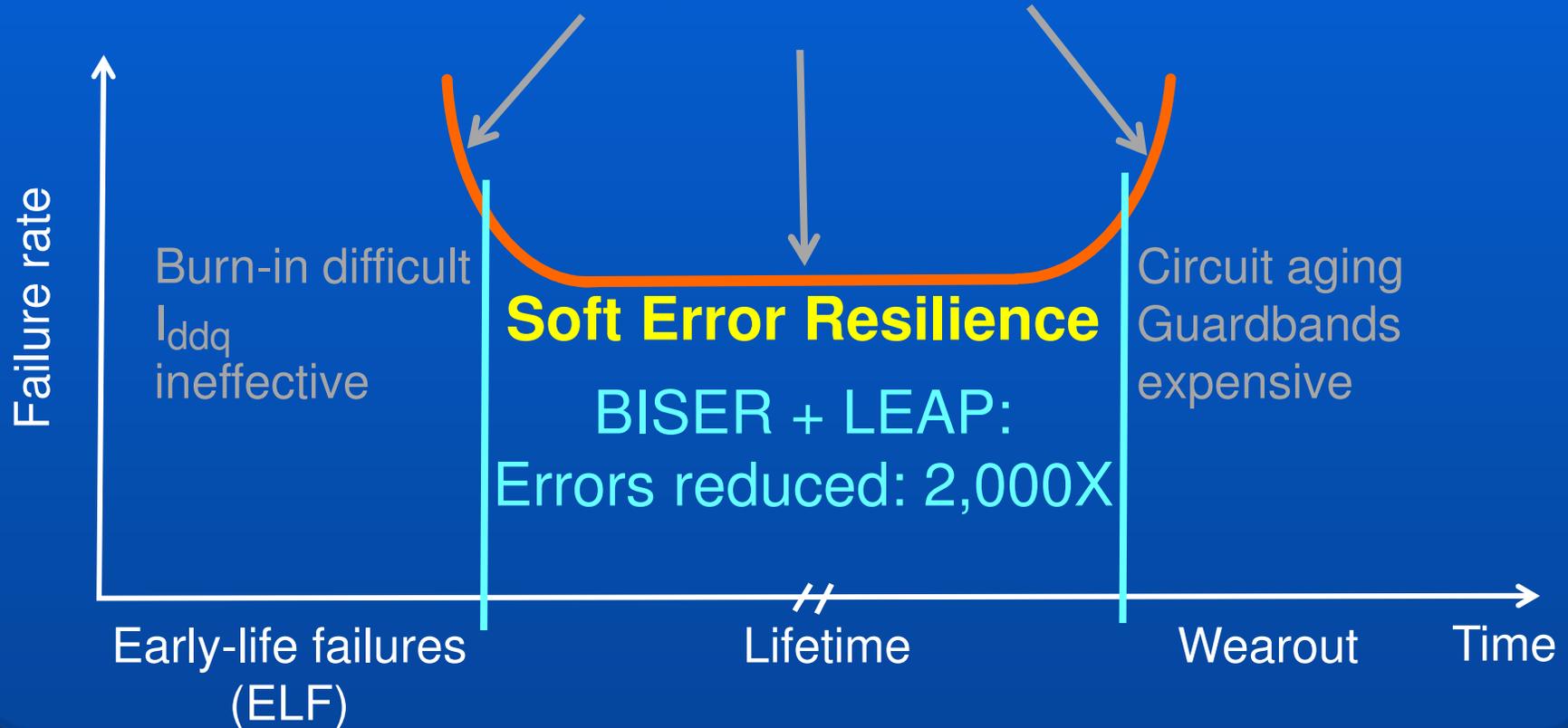
- System soft error rates increasing
 - **Fatal** flip-flop errors
- Early-life failures (ELF)
 - Burn-in: difficult, expensive
- Circuit aging & variations
 - Worst-case guardbands expensive



Low-Cost Resilience

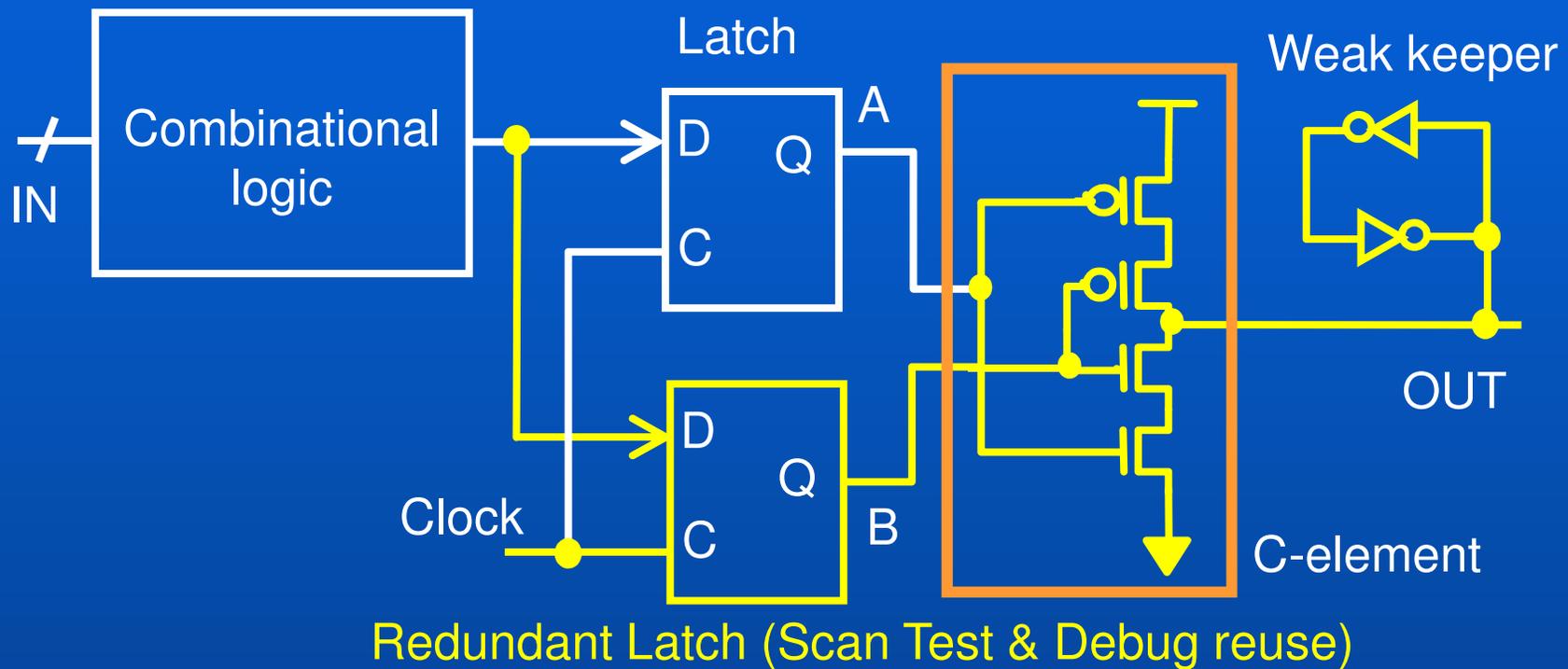
Circuit Failure Prediction

New failure signature → ultra low-cost



Software-orchestrated global optimization a MUST

BISER: Built-In Soft Error Resilience

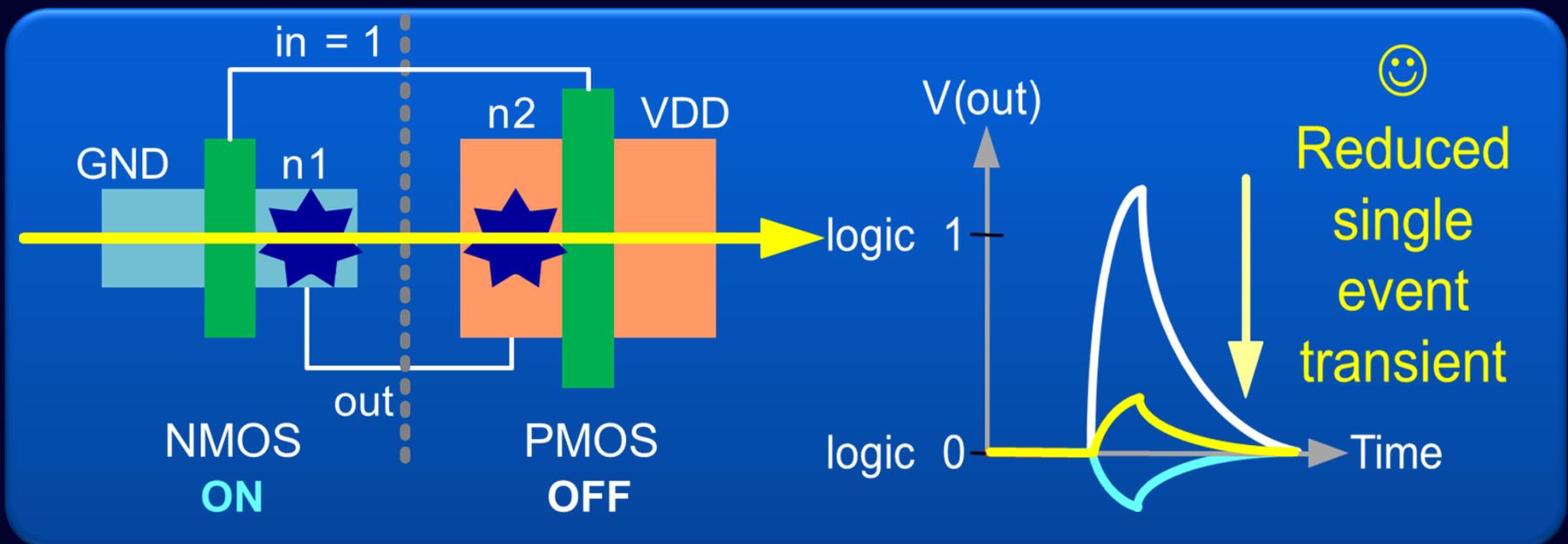


45nm: up to 1,000X fewer errors vs. D-flip-flop

Single Error Assumption Inadequate

- Single event **multiple** upsets increasing

LEAP: Layout by Error Aware transistor Positioning



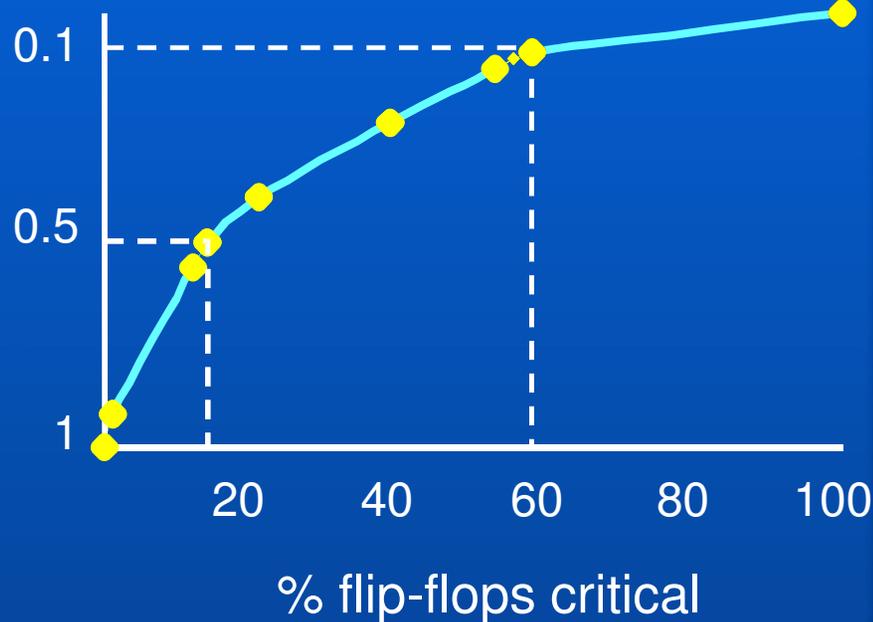
2,000X fewer errors vs. D-flip-flop

Optimized Resilience Essential

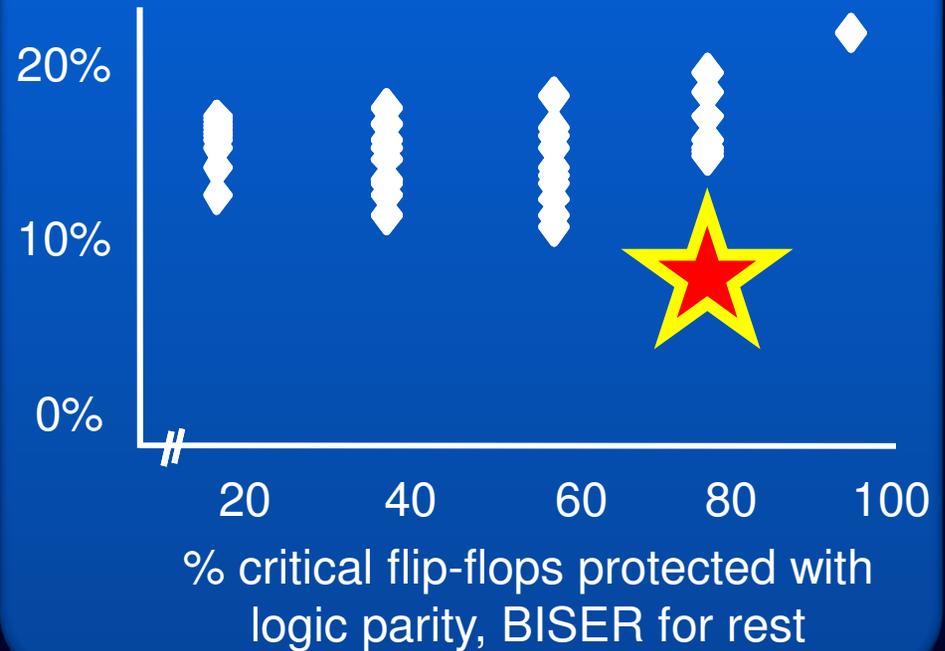
Select application-critical
flip-flops

Optimize for cross-layer
resilience

Chip-level
error rate



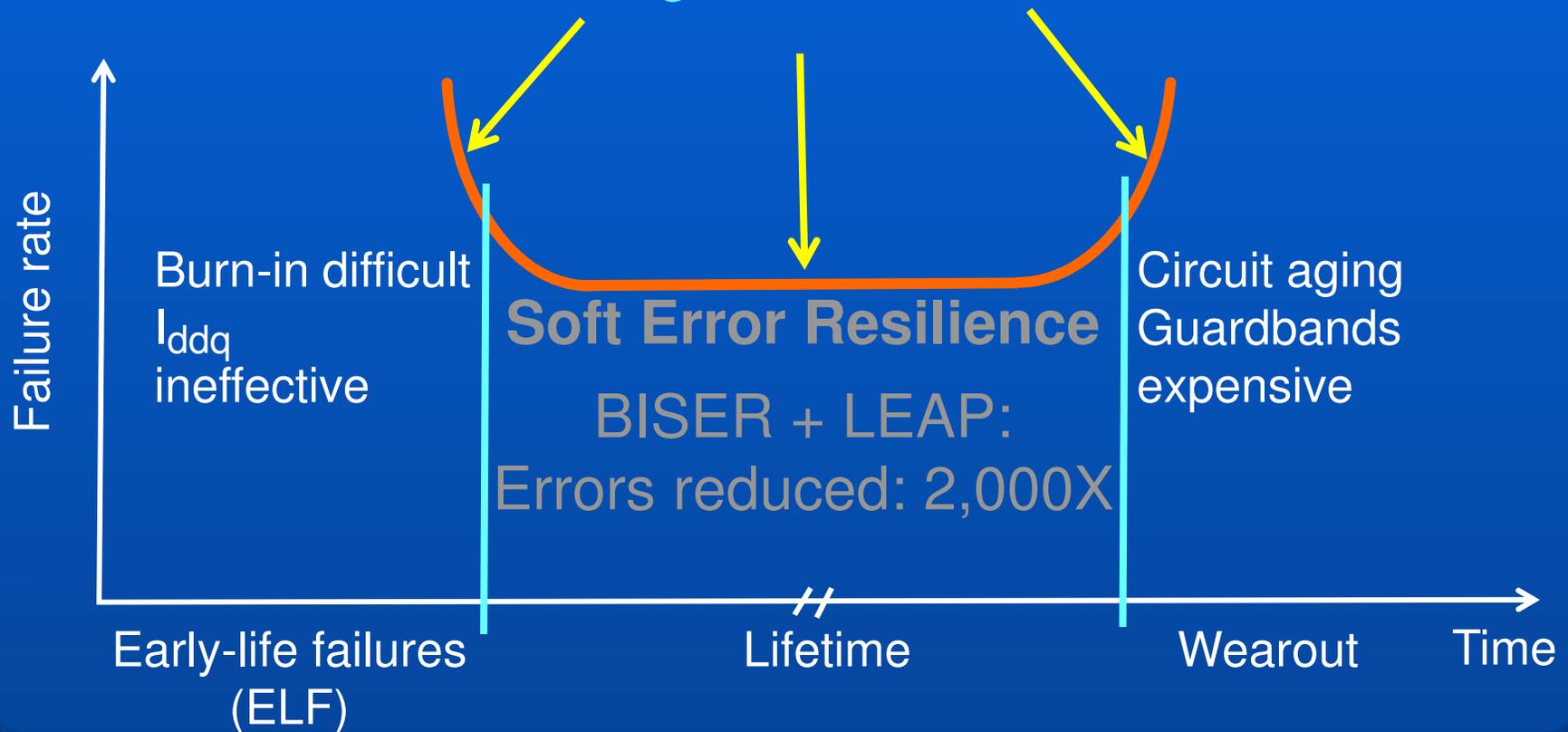
Power
cost



Low-Cost Resilience

Circuit Failure Prediction

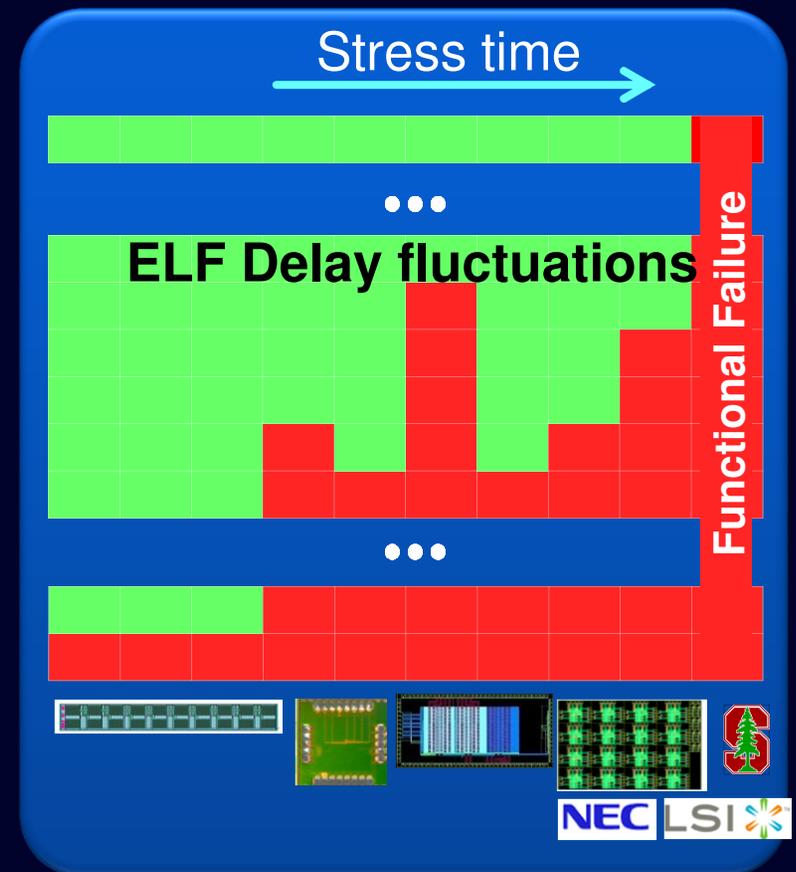
New failure signature → ultra low-cost



Software-orchestrated global optimization a MUST

New Gate-Oxide ELF Signature

- **Delay fluctuations over time**
 - Before functional failure
- Demonstrated: 45, 32nm
 - 28, 22, 15nm in progress
- Enables
 - **On-line failure prediction**



On-line Failure Prediction

Failure Prediction

Error Detection

Before errors appear

After errors appear

+ No corruption

– Corrupt data & states

+ Low cost

– High cost

+ Self-diagnostics

– Limited diagnostics

How ?

On-line self-test and diagnostics

On-Line Self-Test and Diagnostics



On-line self-test & diagnostics

CASP

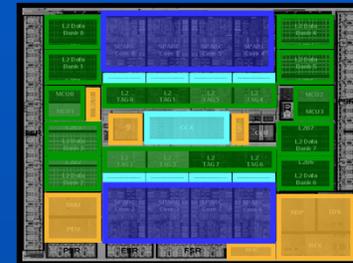
High on-line test coverage

No visible system downtime

1% power, 1% area, 3% performance impact

Ultra low-cost

OpenSPARC T2 SoC

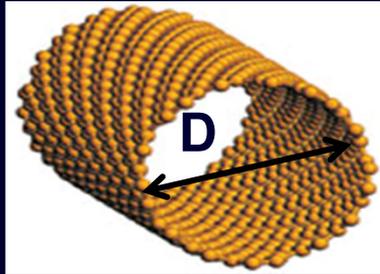


Uncore very important

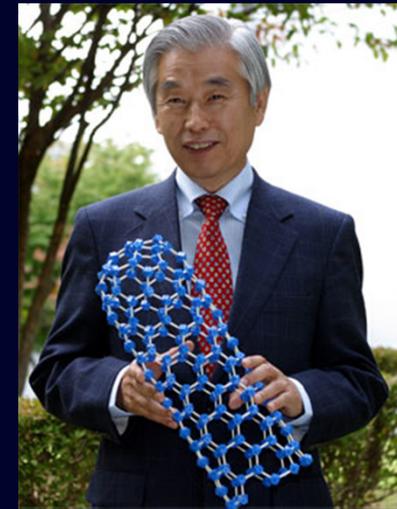
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- CMOS reliability limits: tolerate errors
- **Beyond silicon-CMOS: imperfection-immune logic**
- Conclusion

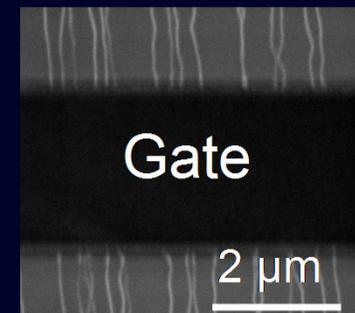
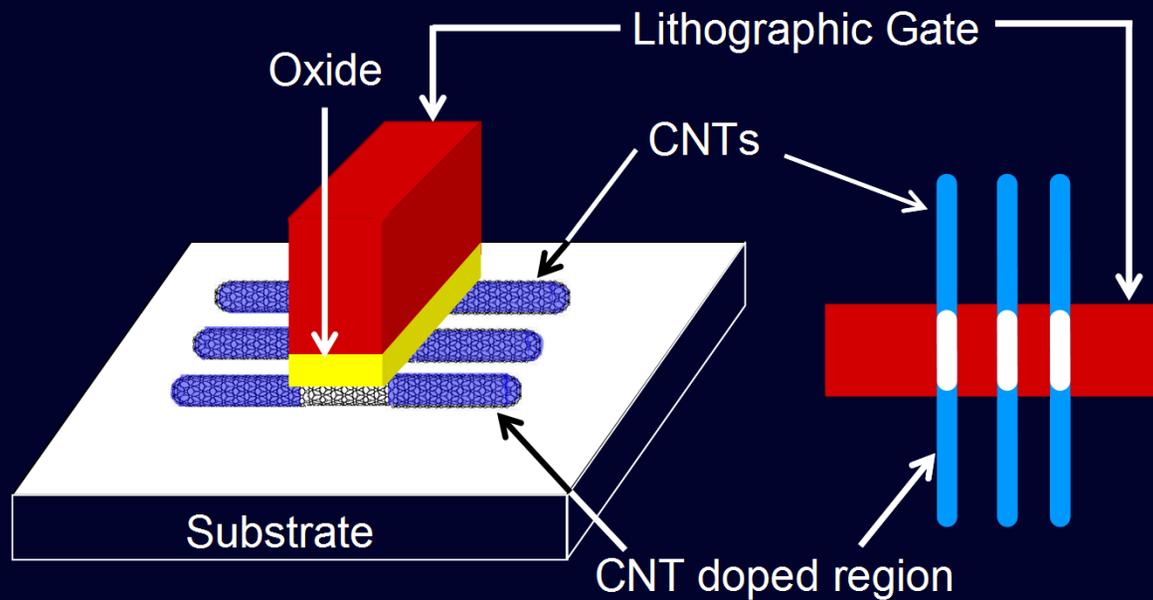
Carbon Nanotube FET (CNFET)



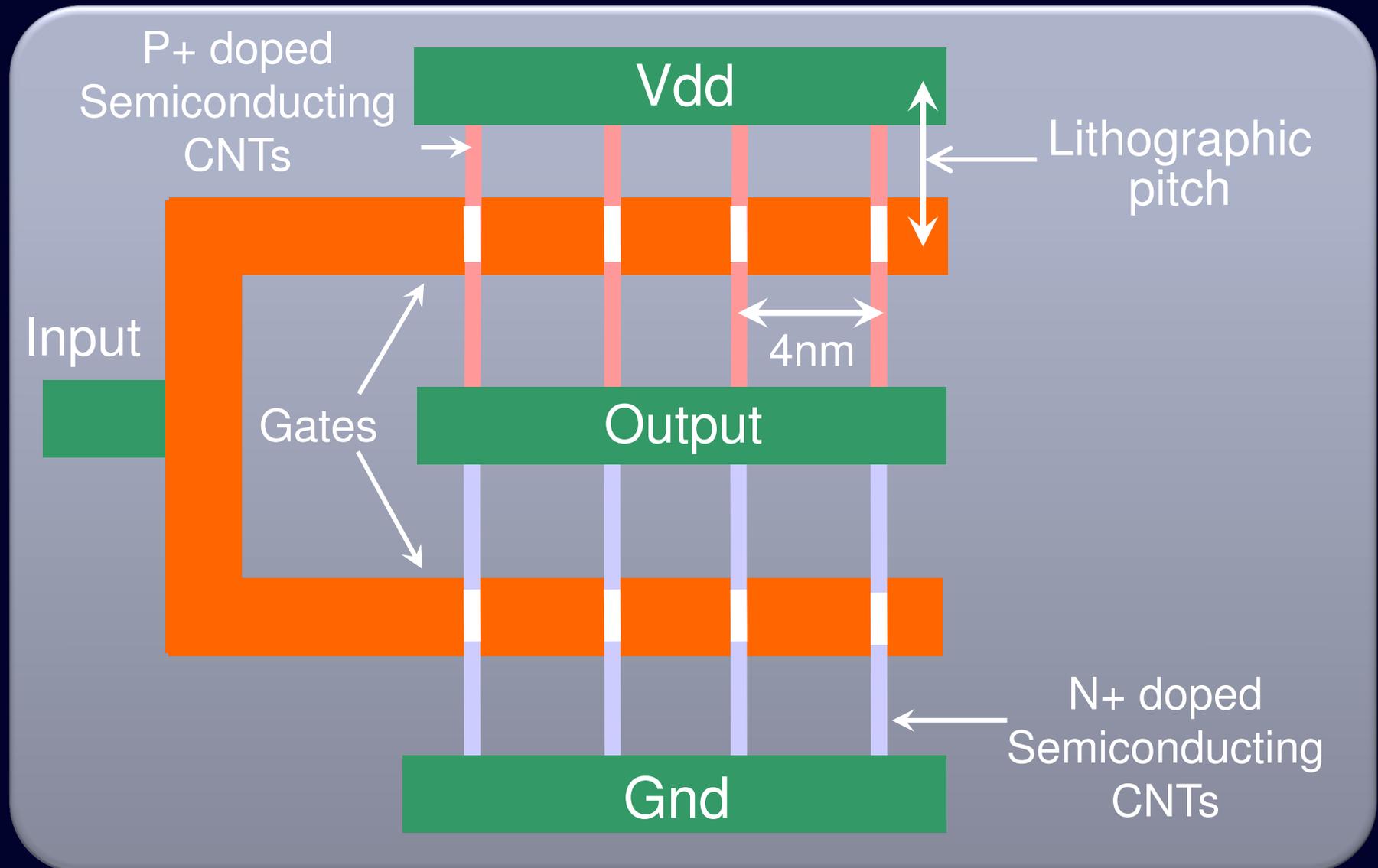
Carbon Nanotube (CNT)
Diameter (D) : 0.5 - 3 nm



S. Iijima

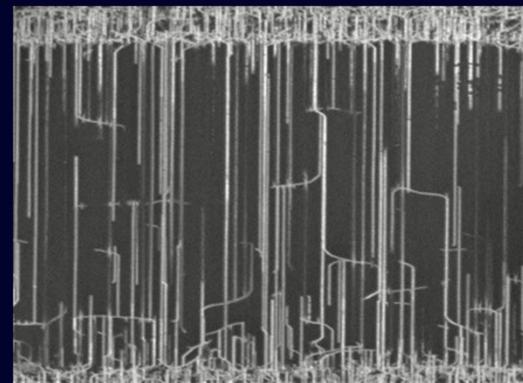


Ideal CNFET Inverter

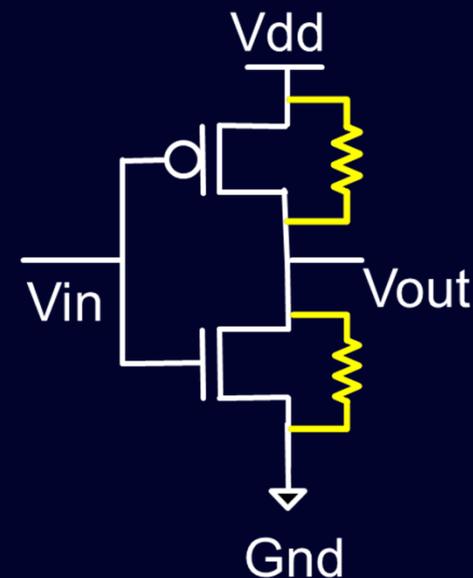


CNFETs: BIG Promise, BUT

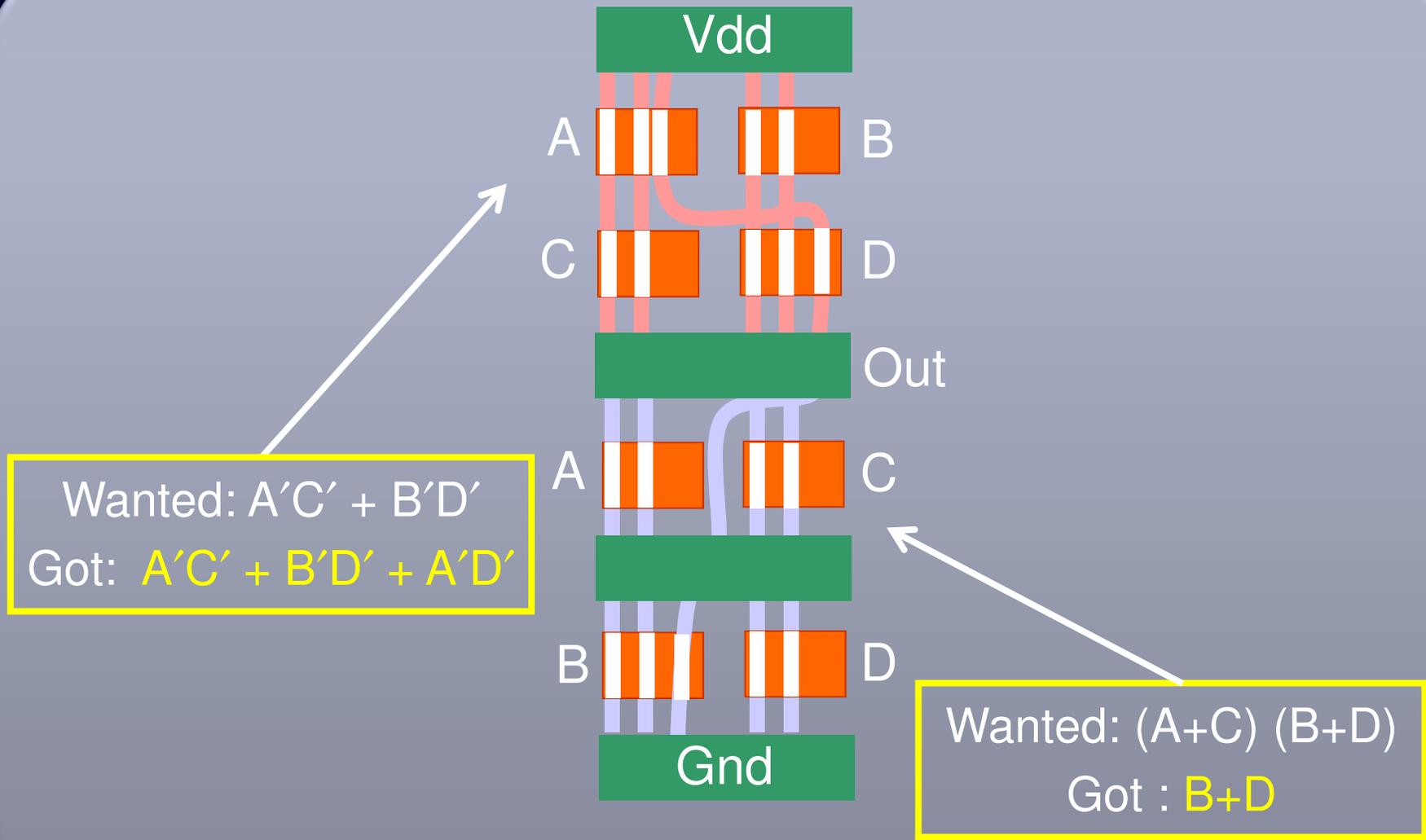
- Major barriers for a decade
 - Mis-positioned CNTs
 - Metallic CNTs
- Processing alone inadequate



**Imperfection-immune
design essential**

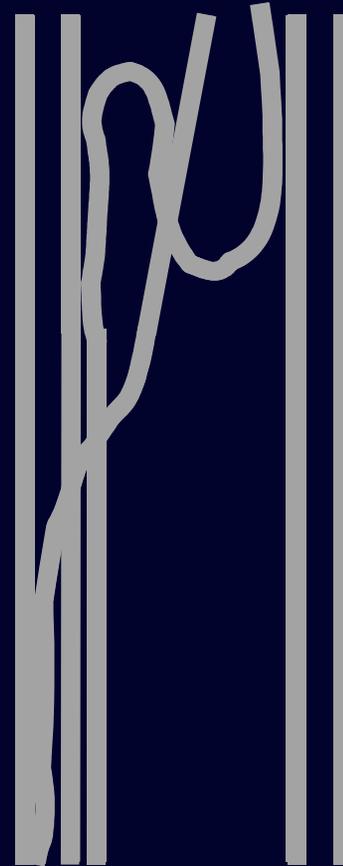


Mis-positioned CNTs: Incorrect Logic



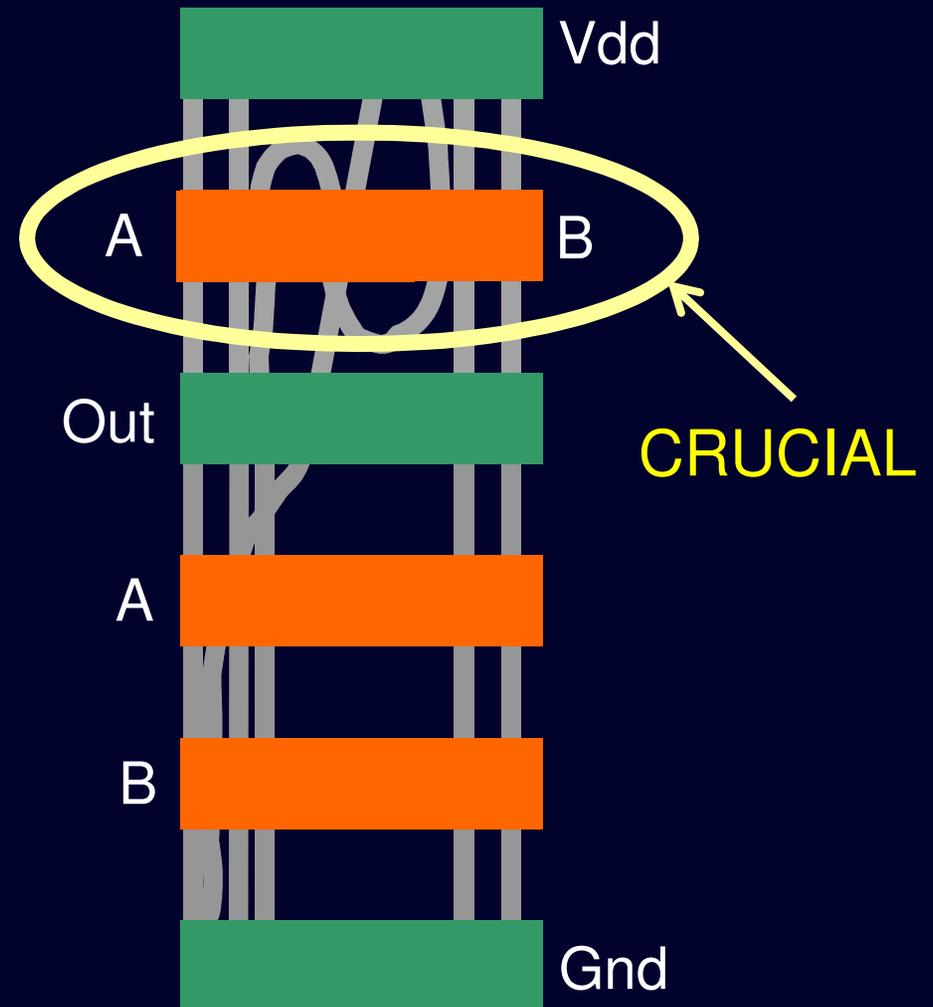
Mis-positioned-CNT-Immune NAND

1. Grow CNTs



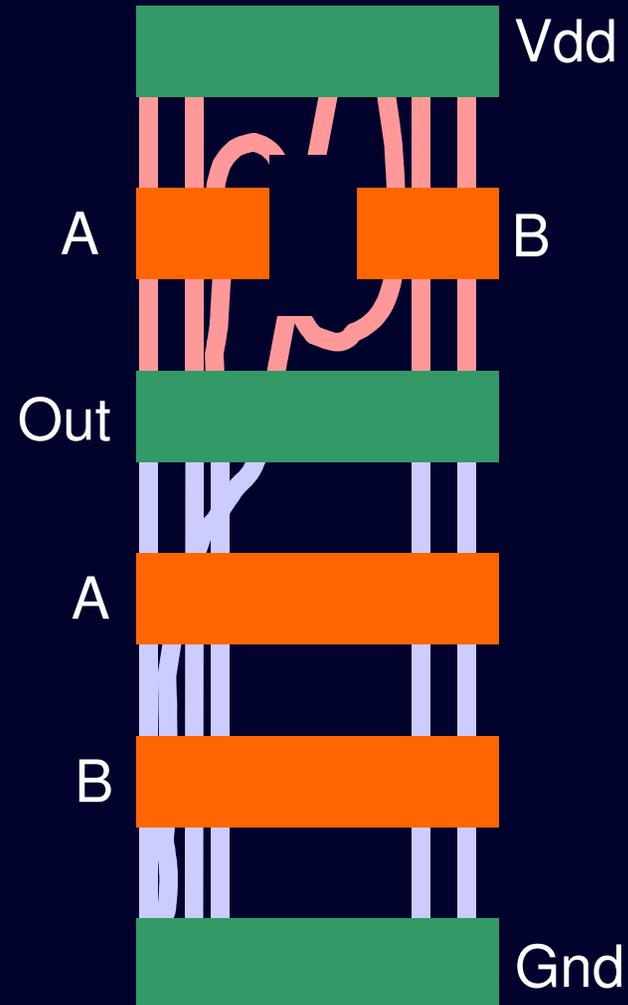
Mis-positioned-CNT-Immune NAND

1. Grow CNTs
2. Extended gate & contacts



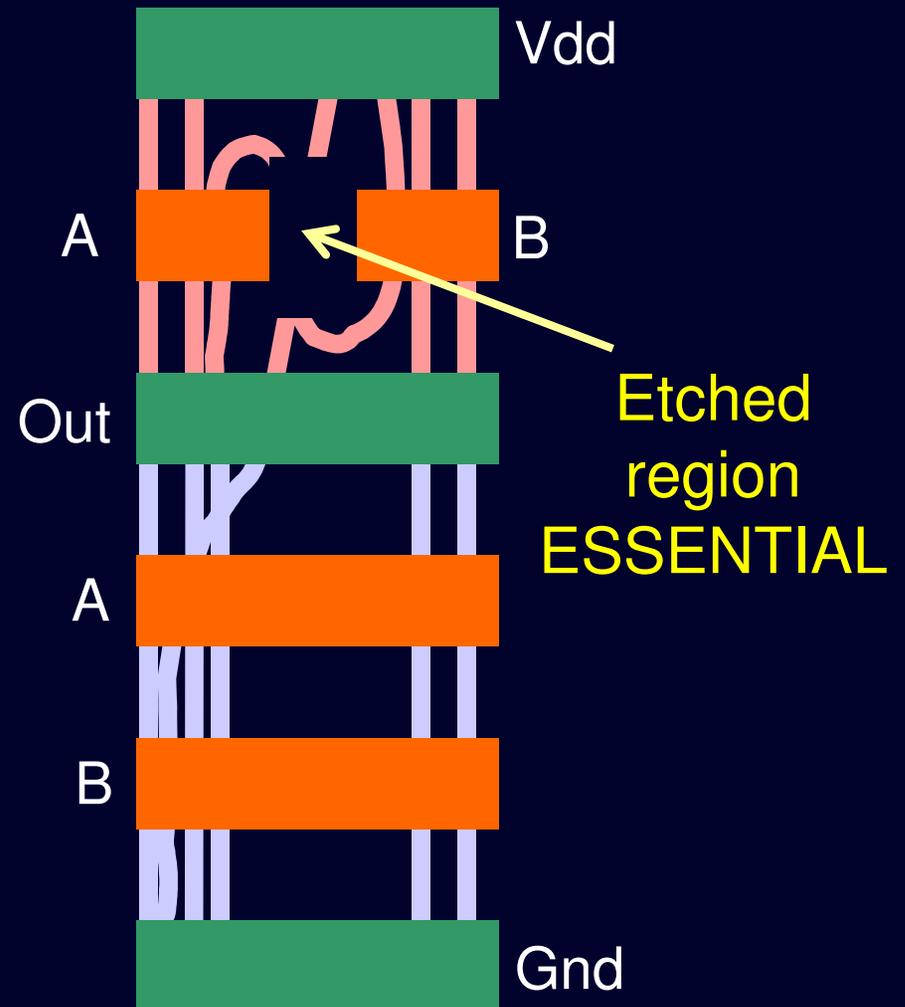
Mis-positioned-CNT-Immune NAND

1. Grow CNTs
2. Extended gate & contacts
3. Etch gate & CNTs
4. Dope P & N regions



Mis-positioned-CNT-Immune NAND

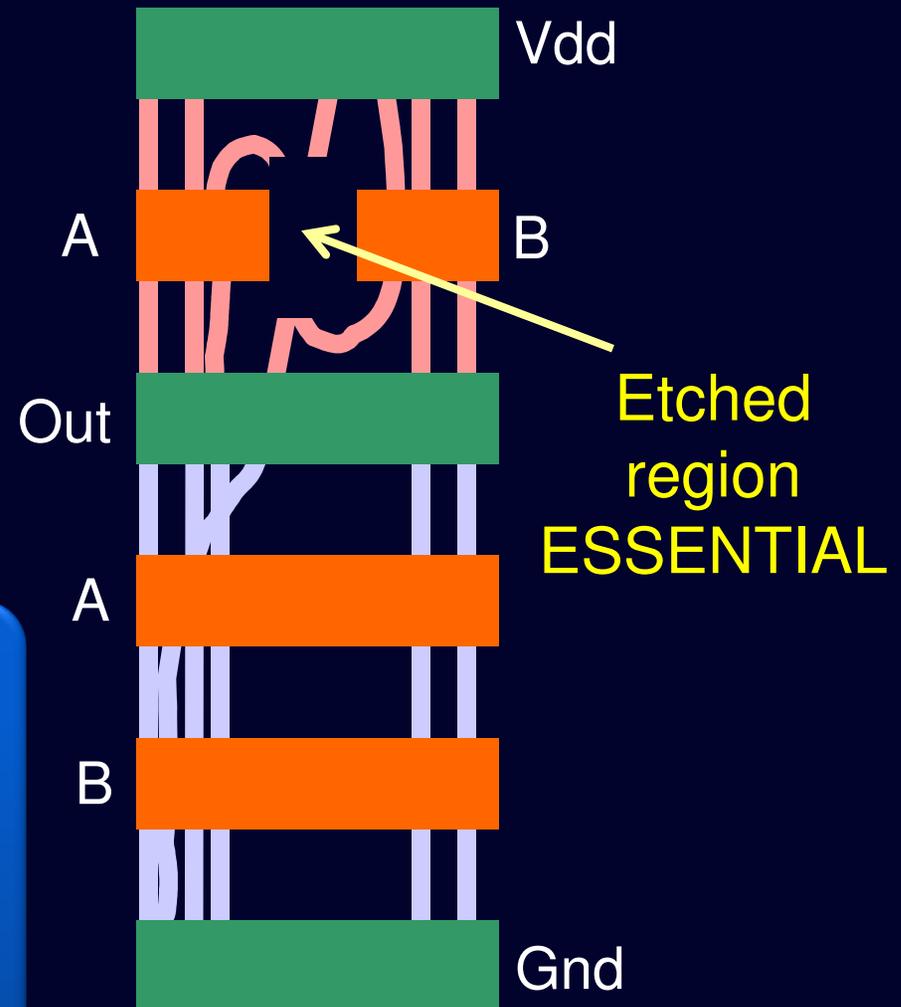
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Mis-positioned-CNT-Immune NAND

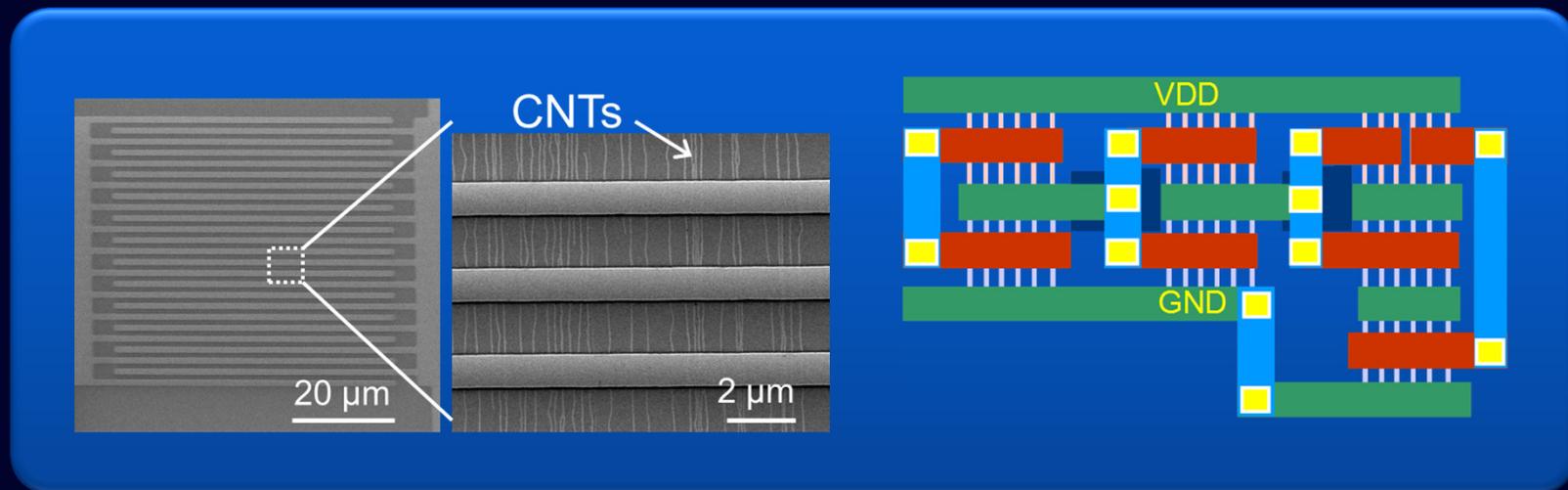
1. Grow CNTs
2. Extended gate & contacts
3. Etch gate & CNTs
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- Graph algorithms
 - All possible functions
- VLSI
 - Processing & design

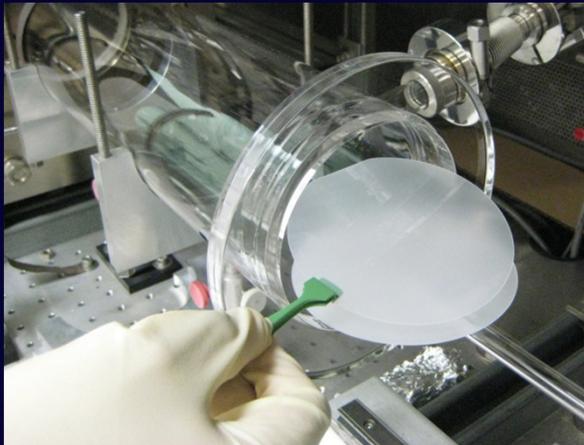


VMR: VLSI Metallic CNT Removal

- Metallic-CNT-immune design
 - ☺ **Sufficient:** all possible logic designs
 - ☺ VLSI processing & design



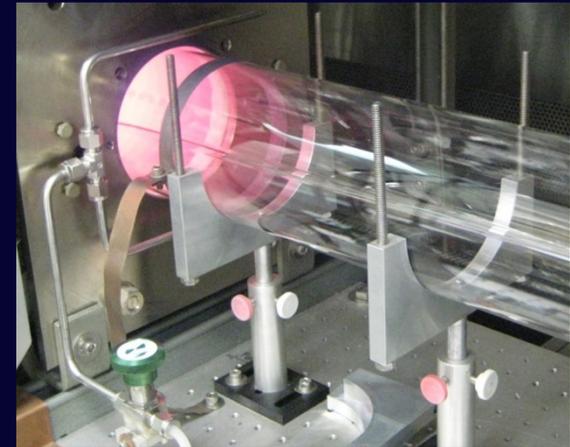
First Wafer-Scale Aligned CNT Growth



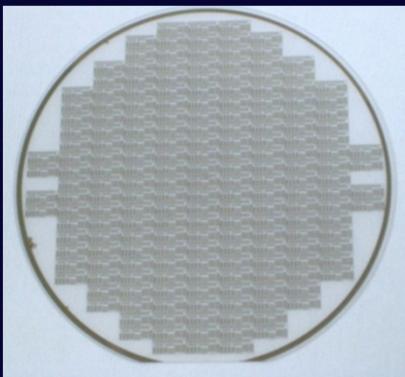
Quartz wafer
with catalyst



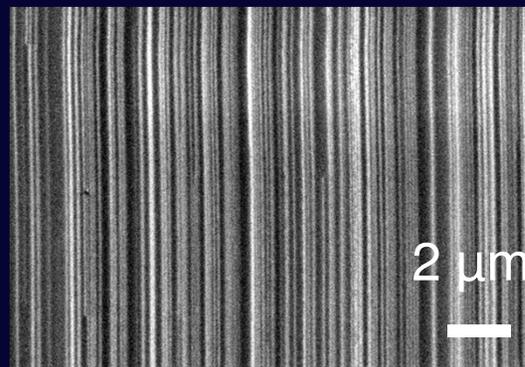
Aligned
CNT growth



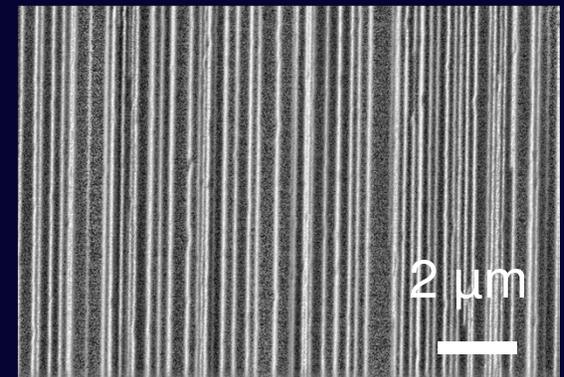
Quartz wafer
99.5% CNTs aligned



Before transfer
Quartz substrate



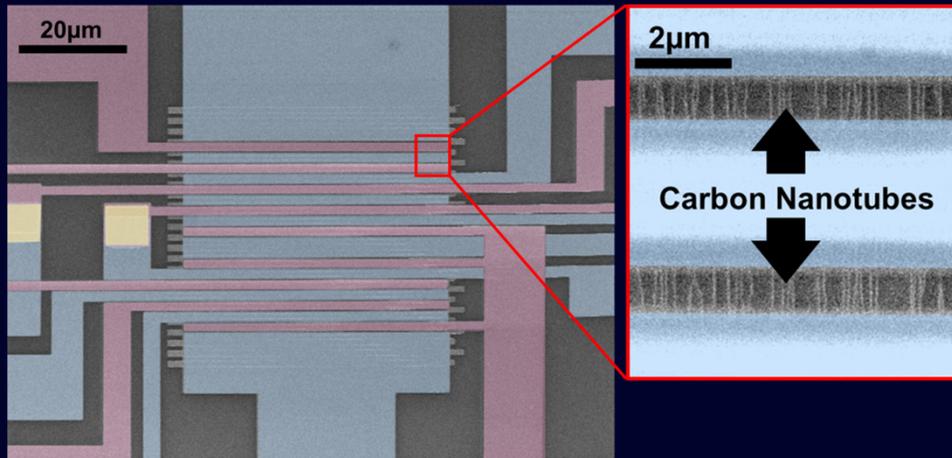
After transfer
SiO₂/Si substrate



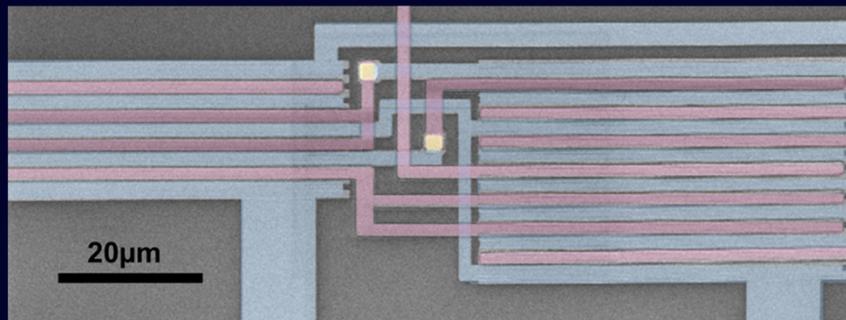
First Experimental Demonstrations

Imperfection-immune circuits

Arithmetic & storage



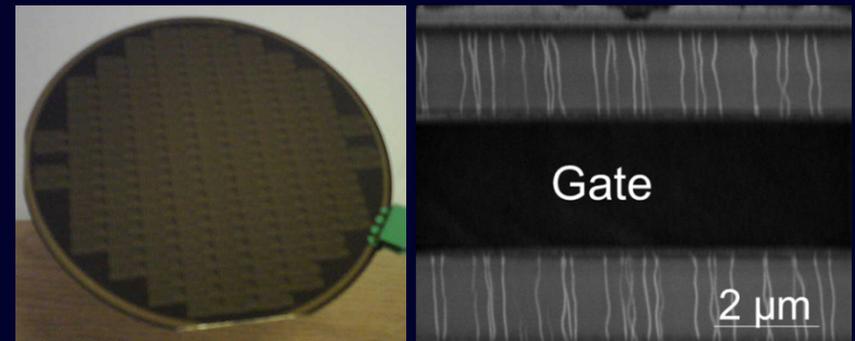
Adder sum



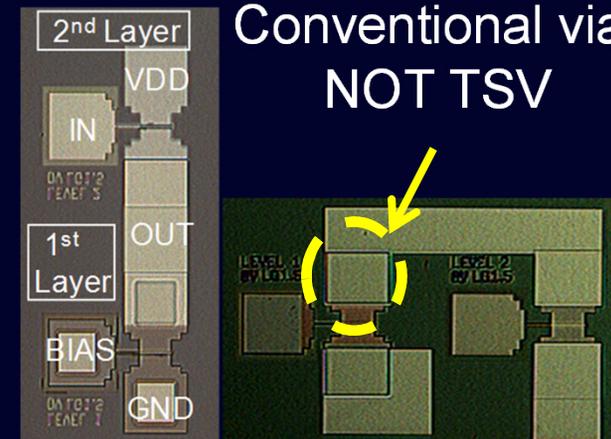
D-latch

VLSI Integration

Wafer-scale & monolithic 3D

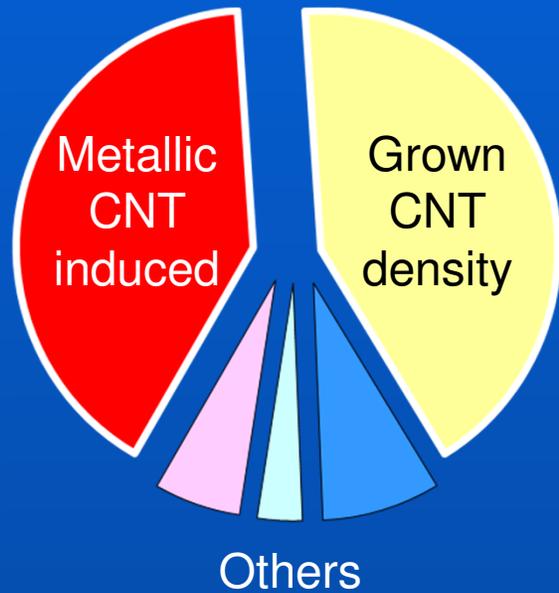


Conventional via,
NOT TSV



Multi-layer CNFET circuits

CNFET Variations Significant



CNFET I_{on} variations

Energy penalty

Very high

Naïve transistor upsizing



No design change

Unique layouts
+ Co-optimized processing

0%

Low (0%)

Yield

High (99%+)

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Thanks to my Research Group



Thanks to our Sponsors



Photo credits:

Burn-in & test socket workshop, H. Dai, NEC, opensparc.net, Stanford

Concluding Remarks

- Derive failure signatures
- Utilize failure signatures
- Validate failure signatures

Enable

Nanotechnology Revolutions

&

A **TRULY Better Tomorrow**